

# Dioda 1N4148 NXP DO35 RoHS szybka,impulsowa 100V,0.1A,<4ns



#### **Dane techniczne:**

Nazwa: 1N4148 Maksymalne napięcie: 100V Maksymalny prąd: 100mA Obudowa: DO-35 Charakterystyka diody: szybka, impulsowa Montaż: przewlekany(THT)

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## DISCRETE SEMICONDUCTORS



Product specification Supersedes data of 1999 May 25 2002 Jan 23



#### **Product specification**

#### 1N4148; 1N4448

#### FEATURES

- Hermetically sealed leaded glass SOD27 (DO-35) package
- High switching speed: max. 4 ns
- General application
- Continuous reverse voltage: max. 75 V
- Repetitive peak reverse voltage: max. 100 V
- Repetitive peak forward current: max. 450 mA.

#### APPLICATIONS

• High-speed switching.

#### LIMITING VALUES

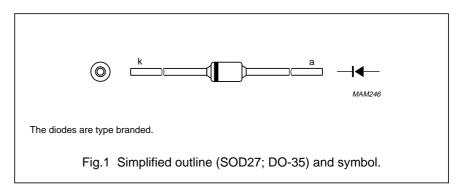
In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V <sub>RRM</sub>	repetitive peak reverse voltage		-	100	V
V <sub>R</sub>	continuous reverse voltage		-	75	V
I <sub>F</sub>	continuous forward current	see Fig.2; note 1	-	200	mA
I <sub>FRM</sub>	repetitive peak forward current		-	450	mA
I <sub>FSM</sub>	non-repetitive peak forward current	square wave; T <sub>j</sub> = 25 °C prior to surge; see Fig.4			
		t = 1 μs	_	4	А
		t = 1 ms	_	1	А
		t = 1 s	-	0.5	A
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> = 25 °C; note 1	-	500	mW
T <sub>stg</sub>	storage temperature		-65	+200	°C
Tj	junction temperature		-	200	°C

#### Note

1. Device mounted on an FR4 printed circuit-board; lead length 10 mm.

The 1N4148 and 1N4448 are high-speed switching diodes fabricated in planar technology, and encapsulated in hermetically sealed leaded glass SOD27 (DO-35) packages.



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#### **ELECTRICAL CHARACTERISTICS**

 $T_i = 25 \ ^{\circ}C$  unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V <sub>F</sub>	forward voltage	see Fig.3			
	1N4148	I <sub>F</sub> = 10 mA	_	1	V
	1N4448	I <sub>F</sub> = 5 mA	0.62	0.72	V
		I <sub>F</sub> = 100 mA	_	1	V
I <sub>R</sub>	reverse current	V <sub>R</sub> = 20 V; see Fig.5		25	nA
		$V_R = 20 \text{ V}; \text{ T}_j = 150 \text{ °C}; \text{ see Fig.5}$	_	50	μA
I <sub>R</sub>	reverse current; 1N4448	V <sub>R</sub> = 20 V; T <sub>j</sub> = 100 °C; see Fig.5	_	3	μA
C <sub>d</sub>	diode capacitance	f = 1 MHz; V <sub>R</sub> = 0; see Fig.6	-	4	pF
t <sub>rr</sub>	reverse recovery time	when switched from $I_F = 10$ mA to $I_R = 60$ mA; $R_L = 100 \Omega$ ; measured at $I_R = 1$ mA; see Fig.7	-	4	ns
V <sub>fr</sub>	forward recovery voltage	when switched from $I_F = 50$ mA; $t_r = 20$ ns; see Fig.8	_	2.5	V

#### THERMAL CHARACTERISTICS

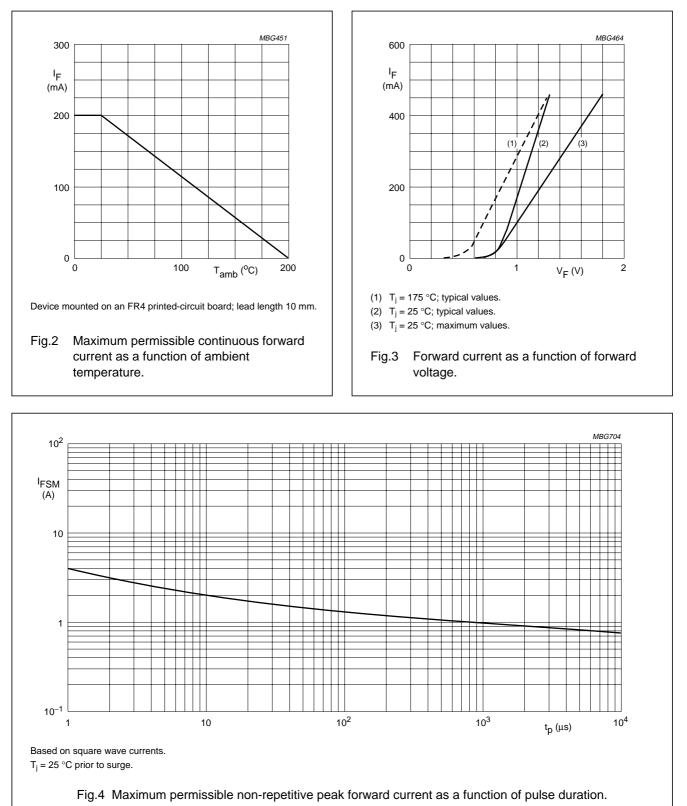
SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R <sub>th j-tp</sub>	thermal resistance from junction to tie-point	lead length 10 mm	240	K/W
R <sub>th j-a</sub>	thermal resistance from junction to ambient	lead length 10 mm; note 1	350	K/W

Note

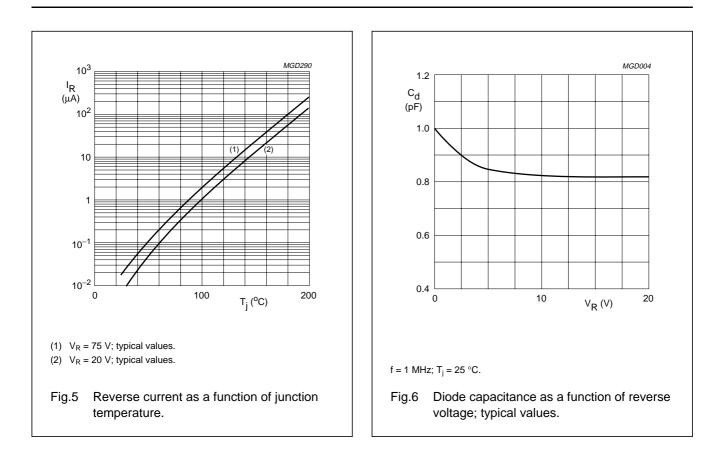
1. Device mounted on a printed circuit-board without metallization pad.

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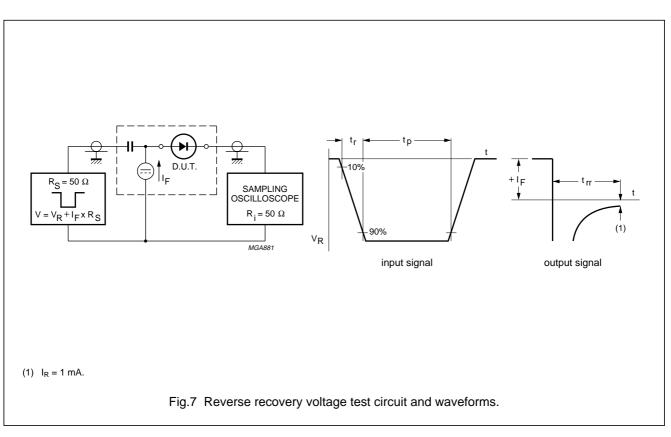
#### **GRAPHICAL DATA**

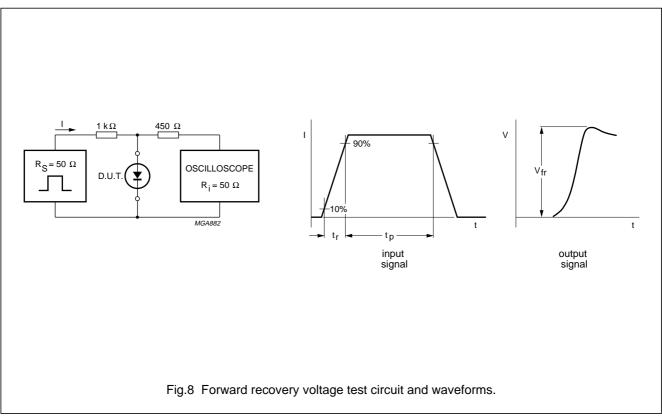


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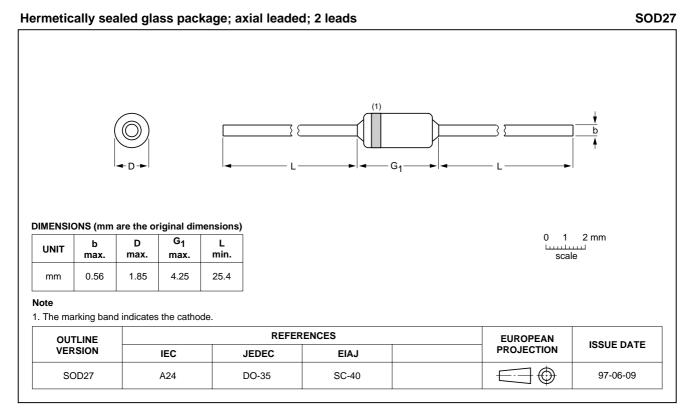
## 1N4148; 1N4448





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#### PACKAGE OUTLINE



#### 1N4148; 1N4448

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DATA SHEET STATUS <sup>(1)</sup>	PRODUCT STATUS <sup>(2)</sup>	DEFINITIONS
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